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January 2015



# FAN6605 mWSaver<sup>™</sup> PWM Controller

#### **Features**

- mWSaver<sup>™</sup> Technology Provides Industry's Best-in-Class Standby Power
  - <100 mW at 25-mW Load for LCDM Adaptor</li>
  - Internal High-Voltage JFET Startup
  - Low Operating Current: Under 2 mA
  - Adaptively Decrease PWM Frequency with Cycle Skipping to 23 kHz at Light-Load Condition for Better Efficiency
  - Feedback Impedance Switching During Minimum Load or No Load
- Proprietary Asynchronous Frequency Hopping Technique that Reduces EMI
- Fixed PWM Frequency: 65 kHz
- Internal Leading-Edge Blanking
- Built-in Synchronized Slope Compensation
- Auto-Restart Protection: Feedback Open-Loop Protection (OLP), V<sub>DD</sub> Over-Voltage Protection (OVP), Over-Temperature Protection (OTP), and Line Over-Voltage Protection
- Soft Gate Drive with Clamped Output Voltage: 18 V
- V<sub>DD</sub> Under-Voltage Lockout (UVLO)
- Programmable Constant Power Limit (Full AC Input Range)
- Internal OTP Sensor with Hysteresis
- Build-in 5-ms Soft-Start Function
- Input Voltage Sensing (V<sub>IN</sub> Pin) for Brown-In/Out Protection with Hysteresis and Line Over-Voltage Protection

#### **Applications**

General-purpose switched-mode power supplies and flyback power converters, including:

- LCD Monitor Power Supply
- Open-Frame SMPS

#### Description

This highly integrated PWM controller provides several features to enhance the performance of flyback converters.

To minimize standby power consumption, a proprietary adaptive green-mode function reduces switching frequency at light-load condition. To avoid acoustic-noise problems, the minimum PWM frequency is set above 23 kHz. This green-mode function enables the power supply to meet international power conservation requirements, such as Energy Star<sup>®</sup>. With the internal high-voltage startup circuitry, the power loss caused by bleeding resistors is also eliminated. To further reduce power consumption, FAN6605 uses the BiCMOS process, which allows an operating current of only 2 mA. The standby power consumption can be under 100 mW for most of LCD monitor power supply designs.

FAN6605 integrates a frequency-hopping function that reduces EMI emission of a power supply with minimum line filters. The built-in synchronized slope compensation achieves a stable peak-current-mode control and improves noise immunity. The proprietary line compensation ensures constant output power limit over a wide AC input voltage range from 90 V<sub>AC</sub> to 264 V<sub>AC</sub>.

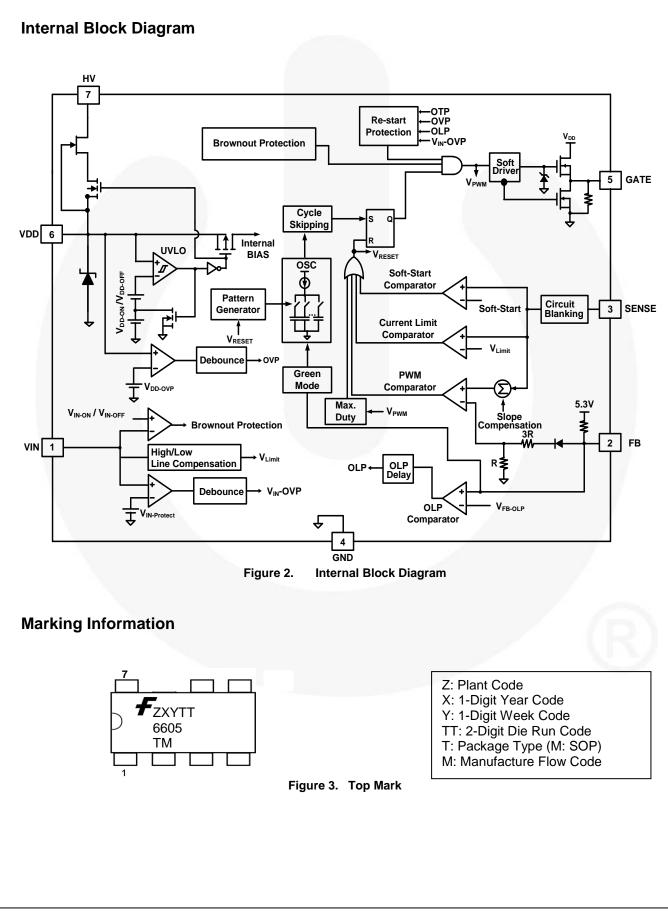
FAN6605 provides many protection functions. The internal feedback open-loop protection circuit protects the power supply from open-feedback-loop condition or output-short condition. It also has line under-voltage protection (brownout protection) and over-voltage protection using an input voltage sensing pin ( $V_{IN}$ ).

FAN6605 is available in a 7-pin SOP package.

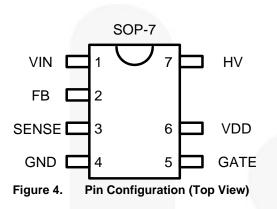
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FAN6
605—
mWSaver™
Controller

Part Number	Operating Temperature Range	Package	PWM Frequency	Packing Method
FAN6605MX	-40 to +105°C	7-Lead, Small Outline Integrated Circuit (SOIC), Depopulated JEDEC MS-112, .150 Inch Body	65 kHz	Reel & Tap
Application	Diagram			
N	EMI Filter			• V0+
L				—° V₀-
			Ŧ	
	FB ↓ 4 ↓ ↓	SENSE 3 W \$	: <	
l		↓ ↓ ↓ ↓ ↓		
		-	- <u>+</u>	
		Figure 1. Typical Application		



# **Pin Configuration**



# **Pin Definitions**

Pin #	Name	Description
1	VIN	Line-voltage detection. The line-voltage detection is used for brownout protection with hysteresis. Constant output power limit over universal AC input range is also achieved using this VIN pin. It is suggested to add a low-pass filter to filter out line ripple on the bulk capacitor. Pulling VIN HIGH also triggers auto-restart protection.
2	FB	The signal from the external compensation circuit is fed into this pin. The PWM duty cycle is determined in response to the signal on this pin and the current-sense signal on the SENSE pin.
3	SENSE	Current sense. The sensed voltage is used for peak-current-mode control and cycle-by-cycle current limiting.
4	GND	Ground
5	GATE	The totem-pole output driver. Soft-driving waveform is implemented for improved EMI.
6	VDD	Power supply. The internal protection circuit disables PWM output as long as $V_{\text{DD}}$ exceeds the OVP trigger point.
7	HV	For startup, this pin is connected to the line input or bulk capacitor in series with resistors.

#### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter		Min.	Max.	Unit
V <sub>VDD</sub>	DC Supply Voltage <sup>(1, 2)</sup>			30	V
V <sub>FB</sub>	FB Pin Input Voltage		-0.3	6.0	V
V <sub>SENSE</sub>	SENSE Pin Input Voltage		-0.3	6.0	V
V <sub>VIN</sub>	VIN Pin Input Voltage		-0.3	6.0	V
V <sub>HV</sub>	HV Pin Input Voltage			700	V
PD	Power Dissipation (T <sub>A</sub> <50°C)			400	mW
$\Theta_{JA}$	Thermal Resistance (Junction-to-Air	)		153	°C/W
TJ	Operating Junction Temperature		-40	+125	°C
T <sub>STG</sub>	Storage Temperature Range		-55	+150	°C
TL	Lead Temperature (Wave Soldering	or IR, 10 Seconds)		+260	°C
ESD	Human Body Model, JEDEC: JESD22-A114	All Pins Except HV Pin		5.5	kV
ESD	Charged Device Model, JEDEC: JESD22-C101	All Pins Except HV Pin		2.0	κV

Notes:

1. All voltage values, except differential voltages, are given with respect to the network ground terminal.

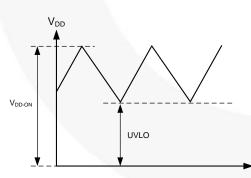
2. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.

3. ESD with HV pin: CDM=2000 V and HBM=3500 V.

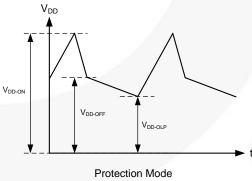
#### **Electrical Characteristics**

 $V_{DD}$ =11~24 V and T<sub>A</sub>=-40~105°C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>DD</sub> Secti	on					
V <sub>OP</sub>	Continuously Operating Voltage	Full Load			22	V
$V_{\text{DD-ON}}$	Start Threshold Voltage		15	16	17	V
$V_{\text{DD-OFF}}$	Protection Mode		9	10	11	V
UVLO	Normal Mode		6.8	7.8	8.8	V
I <sub>DD-ST</sub>	Startup Current	V <sub>DD-ON</sub> – 0.16 V			30	μA
I <sub>DD-OP</sub>	Operating Supply Current	V <sub>DD</sub> =15 V, GATE Open			2	mA
IDD-OLP	Internal Sink Current	V <sub>DD-OLP</sub> +0.1 V	30	60	90	μA
V <sub>DD-OLP</sub>	Threshold Voltage on V <sub>DD</sub> for HV JFET Turn-On		6.5	7.5	8.0	V
V <sub>DD-OVP</sub>	V <sub>DD</sub> Over-Voltage Protection		25	26	27	V
t <sub>D-VDDOVP</sub>	V <sub>DD</sub> Over-Voltage Protection Debounce Time		75	125	200	μs
HV Section	on					
I <sub>HV</sub>	Supply Current Drawn from HV Pin	$V_{DC}$ =120 V, $V_{DD}$ =10 µF, $V_{DD}$ =0 V	2.0	3.5	5.0	mA
I <sub>HV-LC</sub>	Leakage Current after Startup	HV=700 V, V <sub>DD</sub> =V <sub>DD-</sub> <sub>OFF</sub> +1 V		1	20	μA



Normal Mode



Continued on the following page...

Figure 5. V<sub>DD</sub> Behavior

t

#### **Electrical Characteristics**

 $V_{DD}{=}11{\sim}24$  V and  $T_{A}{=}{-}40{\sim}105^{\circ}C$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Oscillato	r Section					
4	Fraguenou in Normal Mada	Center Frequency	62	65	68	
f <sub>OSC</sub>	Frequency in Normal Mode	Hopping Range	±4.5	±5.2	±5.9	kHz
f <sub>OSC-G</sub>	Green-Mode Frequency		20	23	26	kHz
t <sub>HOP</sub>	Hopping Period		10	12	14	ms
t <sub>SKIP-N</sub>	Pulse-Skipping Period <sup>(4)</sup>	V <sub>FB-SKIP</sub> <v<sub>FB<v<sub>FB-N</v<sub></v<sub>	180	200	220	ms
t <sub>SKIP-G</sub>	Pulse-Skipping Period <sup>(4)</sup>	V <sub>FB-G</sub> <v<sub>FB<v<sub>FB-SKIP</v<sub></v<sub>	90			ms
f <sub>DV</sub>	Frequency Variation vs. V <sub>DD</sub> Deviation	V <sub>DD</sub> =11 V to 22 V			5	%
f <sub>DT</sub>	Frequency Variation vs. Temperature Deviation	$T_A=T_J=-40$ to $105^{\circ}C$			5	%
V <sub>IN</sub> Section	on					
V <sub>IN-OFF</sub>	PWM Turn-Off (Brownout) Threshold Voltage		0.66	0.70	0.74	V
V <sub>IN-ON</sub>	PWM Turn-On (Brown-in) Threshold Voltage		V <sub>IN-OFF</sub> + 0.17	V <sub>IN-OFF</sub> + 0.20	V <sub>IN-OFF</sub> + 0.23	V
V <sub>IN-Protect</sub>	Threshold Voltage of V <sub>IN</sub> Over- Voltage Protection		5.1	5.3	5.5	V
t <sub>VIN-Protect</sub>	Debounce Time of V <sub>IN</sub> Over- Voltage Protection		60	100	140	μs
Current-	Sense Section			1		
V <sub>LIMIT</sub> at V <sub>IN</sub> =1 V	Threshold Voltage for Current Limit	V <sub>IN</sub> =1 V	0.80	0.83	0.86	V
V <sub>LIMIT</sub> at V <sub>IN</sub> =3 V	Threshold Voltage for Current Limit	V <sub>IN</sub> =3 V	0.67	0.70	0.73	V
t <sub>PD</sub>	Delay to Output			100	200	ns
t <sub>LEB</sub>	Leading-Edge Blanking Time	Steady State	240	290	340	ns
t <sub>SS</sub>	Period During Soft-Start Time	Startup Time	4.0	5.5	7.0	ms

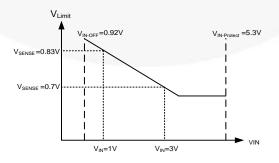


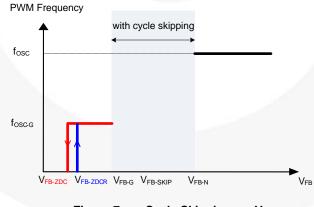
Figure 6. V<sub>IN</sub> vs. V<sub>SENSE</sub>

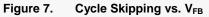
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## **Electrical Characteristics**

 $V_{\text{DD}}\text{=}11\text{-}24$  V and  $T_{\text{A}}\text{=}\text{-}40\text{-}105^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Feedbac	k Input Section		•			
Av	Internal FB Voltage Attenuation		1/4.5	1/4.0	1/3.5	V/V
$Z_{FB}$	Input Impedance	V <sub>FB</sub> =4 V	10	15	19	kΩ
$V_{FB}$ -Open	The Maximum Clamp of FB Voltage	FB Pin Open	5.1	5.3	5.5	V
$V_{FB-OLP}$	FB Open-Loop Protection Triggering Level	T <sub>A</sub> =25°C	4.4	4.6	4.8	V
t <sub>D-OLP</sub>	Delay Time of FB Pin Open-loop Protection		45.0	62.5	70.0	ms
$V_{FB-N}$	Green-Mode Entry FB Voltage		2.8	3.0	3.2	V
$V_{FB-G}$	Green-Mode Ending FB Voltage			V <sub>FB-N</sub> - 0.6		V
V <sub>FB-SKIP</sub>	FB Threshold Voltage for Changing Pulse-Skipping Period <sup>(4)</sup>		2.5	2.7	2.9	V
V <sub>FB-ZDCR</sub>	FB Threshold Voltage for Zero-Duty Recovery		1.6	1.8	2.0	V
V <sub>FB-ZDC</sub>	FB Threshold Voltage for Zero-Duty		1.4	1.6	1.8	V
V <sub>FB-ZDCR</sub> - V <sub>FB</sub> -zdc	ZDC Hysteresis		0.12	0.15	0.19	V





Continued on the following page...

### **Electrical Characteristics**

 $V_{DD}{=}11{\sim}24$  V and  $T_{A}{=}{-}40{\sim}105^{\circ}C$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
GATE Se	ction			1	I	
DCY <sub>MAX</sub>	Maximum Duty Cycle		60	75	90	%
$V_{\text{GATE-L}}$	Gate Low Voltage	V <sub>DD</sub> =15 V, I <sub>O</sub> =50 mA			1.5	V
$V_{\text{GATE-H}}$	Gate High Voltage	V <sub>DD</sub> =12 V, I <sub>O</sub> =50 mA	8			V
tr	Gate Rising Time	V <sub>DD</sub> =15 V, C <sub>L</sub> =1 nF		100		ns
t <sub>f</sub>	Gate Falling Time	V <sub>DD</sub> =15 V, C <sub>L</sub> =1 nF		30		ns
I <sub>GATE-</sub> SOURCE	Gate Source Current	V <sub>DD</sub> =15 V, GATE=6 V		700		mA
V <sub>GATE-</sub> CLAMP	Gate Output Clamping Voltage	V <sub>DD</sub> =22 V			18	V
Over-Ten	nperature Protection Section (OT	P)				
TOTP	Protection Junction Temperature <sup>(5,7)</sup>			125		°C
T <sub>Restart</sub>	Restart Junction Temperature <sup>(6,7)</sup>			T <sub>OTP</sub> -25		°C

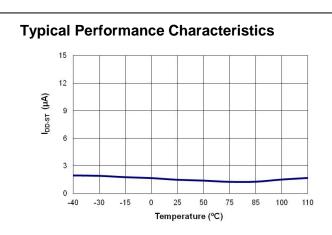
#### Notes:

4.

5.

Guarantee by design. When OTP is activated, the PWM switching is shut down. When junction temperature is lower than this level, IC resumes PWM switching. 6.

These parameters are guaranteed by design. 7.



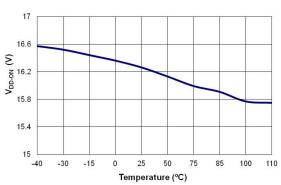
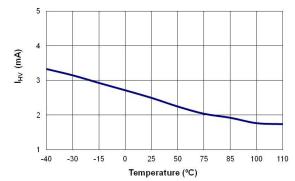
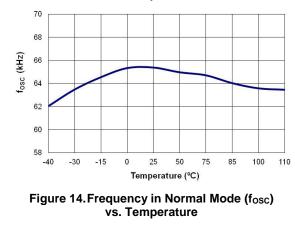


Figure 8. Startup Current (I<sub>DD-ST</sub>) vs. Temperature

Figure 10. Start Threshold Voltage (V<sub>DD-ON</sub>) vs. Temperature







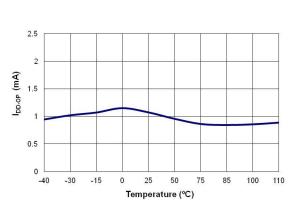


Figure 9. Operation Supply Current (IDD-OP) vs. Temperature

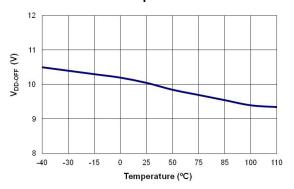


Figure 11. Minimum Operating Voltage (VDD-OFF) vs. Temperature

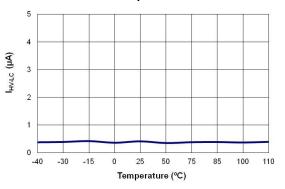
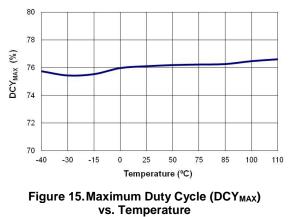


Figure 13.HV Pin Leakage Current After Startup (I<sub>HV-LC</sub>) vs. Temperature



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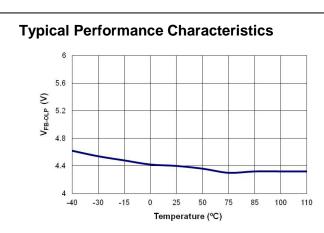


Figure 16.FB Open-Loop Trigger Level (V<sub>FB-OLP</sub>) vs. Temperature

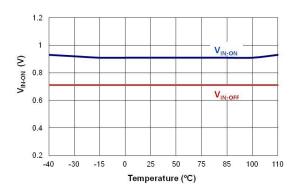


Figure 18.PWM Turn-Off Threshold Voltage (V<sub>IN-OFF</sub> & V<sub>IN-ON</sub>) vs. Temperature

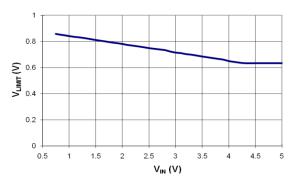


Figure 20. VIN vs. VLIMIT

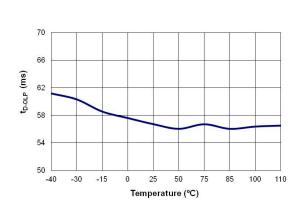


Figure 17.Delay Time of FB Pin Open-Loop Protection (t<sub>D-OLP</sub>) vs. Temperature

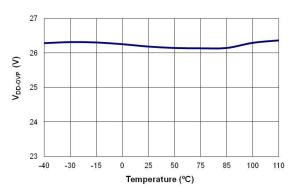


Figure 19.V<sub>DD</sub> Over-Voltage Protection (V<sub>DD-OVP</sub>) vs. Temperature

#### **Functional Description**

#### **Startup Current**

For startup, the HV pin is connected to the line input or bulk capacitor in series with diodes and/or resistors. If HV pin is connected to the line input, a 1-kV/ 1-A diode and a 100 k $\Omega$  resistor are recommended. If HV pin is connected to the bulk capacitor, only the resistor is required. Startup current drawn from pin HV (typically 3.5 mA) charges the hold-up capacitor through the diode and resistor. When the V\_{DD} capacitor level reaches V\_{DD-ON}, the startup current switches off. At this moment, only the VDD capacitor supplies the FAN6605 to maintain V\_{DD} before the auxiliary winding of the main transformer to provide the operating current.

#### **Operating Current**

Operating current is below 2 mA. The low operating current enables better efficiency and reduces the requirement of  $V_{DD}$  hold-up capacitance.

#### **Green-Mode Operation**

The proprietary green-mode function provides an offtime modulation to reduce the switching frequency in light-load and no-load conditions. The on time is limited for better abnormal or brownout protection.  $V_{FB}$ , which is derived from the voltage feedback loop, is taken as the reference. Once  $V_{FB}$  is lower than the threshold voltage, switching frequency is continuously decreased with cycle skipping to the minimum green-mode frequency of around 23 kHz.

#### **Current Sensing / PWM Current Limiting**

Peak-current-mode control is utilized to regulate output voltage and provide pulse-by-pulse current limiting. The switching current is detected by the current-sensing resistor of SENSE pin. The PWM duty cycle is determined by this current sense signal and V<sub>FB</sub>, the feedback voltage. When the voltage on the SENSE pin reaches around V<sub>COMP</sub>=(V<sub>FB</sub>-0.6)/4, the PWM switching turns off immediately.

#### Leading-Edge Blanking (LEB)

Each time the power MOSFET is switched on, a turn-on spike occurs on the sense resistor. To avoid premature termination of the switching pulse, a leading-edge blanking time is built in. During this blanking period, the current-limit comparator is disabled and cannot switch off the gate driver.

#### **Under-Voltage Lockout (UVLO)**

The turn-on and turn-off thresholds are fixed internally at 16 V and 7.8 V in normal mode. During startup, the hold-up capacitor must be charged to 16 V through the startup resistor to enable the IC. The hold-up capacitor continues to supply  $V_{DD}$  before the energy can be delivered from auxiliary winding of the main transformer.  $V_{DD}$  must not drop below 7.8 V during startup. This UVLO hysteresis window ensures that the hold-up capacitor is adequate to supply  $V_{DD}$  during startup.

#### Gate Output / Soft Driving

The BiCMOS output stage is a fast totem-pole gate driver. Cross conduction has been avoided to minimize heat dissipation, increase efficiency, and enhance reliability. The output driver is clamped by an internal 18 V Zener diode to protect power MOSFET transistors against undesirable gate over-voltage. A soft-driving circuit is implemented to minimize EMI.

#### Soft-Start

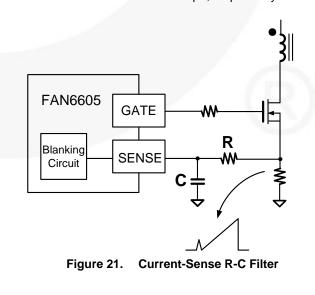
For many applications, it is necessary to minimize the inrush current at startup. The built-in 5.5 ms soft-start circuit significantly reduces the startup current spike and output voltage overshoot.

#### **Slope Compensation**

The sensed voltage across the current-sense resistor is used for peak-current-mode control and pulse-by-pulse current limiting. Built-in slope compensation improves stability and prevents sub-harmonic oscillation. FAN6605 inserts a synchronized positive-going ramp at every switching cycle as slope compensation.

#### **Constant Output Power Limit**

For constant output power limit over universal inputvoltage range, the peak-current threshold is adjusted by the voltage of the VIN pin. Since the VIN pin is connected to the rectified AC input line voltage through the resistive divider, a higher line voltage generates a higher V<sub>IN</sub> voltage. The threshold voltage decreases as V<sub>IN</sub> increases, making the maximum output power at high-line input voltage equal to that at low-line input. The value of R-C network should not be so large that it affects the power limit (shown in Figure 21). R and C should be less than 100  $\Omega$  and 470 pF, respectively.



#### **V<sub>DD</sub> Over-Voltage Protection**

 $V_{DD}$  over-voltage protection prevents damage due to abnormal conditions. Once the  $V_{DD}$  voltage is over the over-voltage protection voltage ( $V_{DD-OVP}$ ), and lasts for  $t_D$ .  $v_{DDDOVP}$ , the PWM pulses are disabled. When the  $V_{DD}$  voltage drops below the UVLO, the internal startup circuit turns on, and  $V_{DD}$  is charged to  $V_{DD-ON}$  to restart IC.

#### Feedback Impedance Switching

FAN6605 actively varies FB-pin impedance ( $Z_{FB}$ ) to reduce no-load power consumption. This technique can further reduce operating current of the controller when FB-pin voltage drops below V<sub>FB-ZDC</sub>.

#### **Brownout Protection**

Since the VIN pin is connected through a resistive divider to the rectified AC input line voltage, it can also be used for brownout protection. If  $V_{IN}$  is less than 0.7 V, the PWM output is shut off. When  $V_{IN}$  reaches over 0.9 V, the PWM output is turned on again. The hysteresis window for ON/OFF is around 0.2 V. The brownout voltage setting is determined by the potential divider formed with  $R_{Upper}$  and  $R_{Lower}$ . Equations to calculate the resistors are shown below:

$$V_{IN} = \frac{R_{Lower}}{R_{Lower} + R_{Upper}} \times V_{AC} \sqrt{2}, (unit = V)$$
(1)

#### **Thermal Overload Protection**

Thermal overload protection limits total power dissipation. When the junction temperature exceeds  $T_{J}$ = +140°C, the thermal sensor signals the shutdown logic

and turns off most of the internal circuitry. The thermal sensor turns internal circuitry on again after the IC's junction temperature drops by 25°C. Thermal overload protection is designed to protect the FAN6605 in the event of a fault condition. For continual operation, the controller should not exceed the absolute maximum junction temperature of  $T_J = +140$ °C.

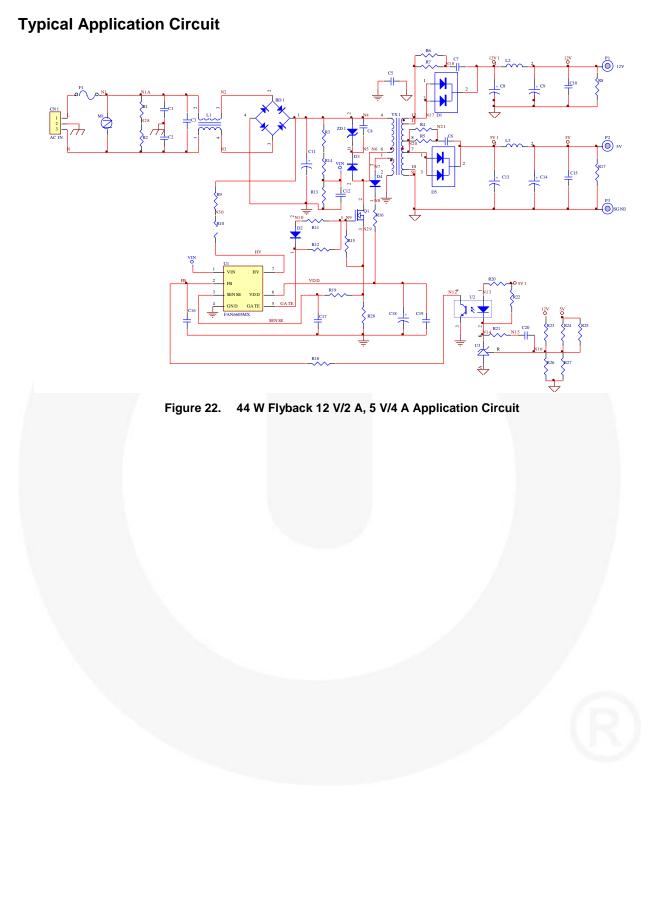
#### **Limited Power Control**

The FB voltage is saturated HIGH when the power supply output voltage drops below its nominal value and shunt regulator (KA431) does not draw current through the opto-coupler. This occurs when the output feedback loop is open or output is short circuited. If the FB voltage is higher than a built-in threshold for longer than  $t_{D-OLP}$ , PWM output is turned off. As PWM output is turned off,  $V_{DD}$  begins decreasing since no more energy is delivered from the auxiliary winding.

As the protection is triggered, VDD enters into UVLO mode. This protection feature continues as long as the over loading condition persists. This prevents the power supply from overheating due to overloading conditions.

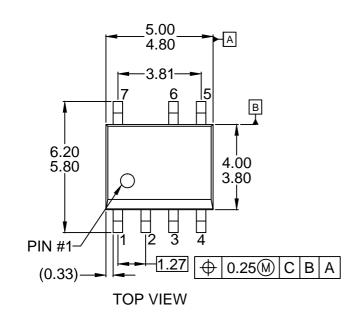
#### **Noise Immunity**

Noise on the current sense or control signal may cause significant pulse-width jitter, particularly in continuousconduction mode. Slope compensation helps alleviate this problem. Good placement and layout practices should be followed. Avoiding long PCB traces and component leads, locating compensation and filter components near the FAN6605, and increasing the gate resistor from GATE pin to MOSFET improve performance.



FAN6605
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Controller

Designator	Part Type	Designator	Part Type	
BD1	BD 4 A/600 V	Q1	MOS 9 A/600 V	
C1	YC 2200 pF/Y1	R1	R 1.5 MΩ 1/4 W	
C2	YC 2200 pF/Y1	R2	R 1.5 MΩ 1/4 W	
C3	XC 0.33 µF/300 V	R3	R 10 MΩ 1/4 W	
C4	NC	R4, R5, R6, R7	R 47 Ω 1/4 W	
C5	YC 2200 pF/Y1	R8, R17, R25, R27	NC	
C6	CC 2200 pF/100 V	R9	R 50 KΩ 1/4 W	
C7	CC 1000 pF/100 V	R10	R 50 KΩ 1/4 W	
C8	EC 1000 µF/25 V	R11	R 0 Ω 1/8 W	
C9	EC 470 µF/25 V	R12	R 47 Ω 1/8 W	
C10	CC 100 pF/50 V	R13	R 100 KΩ 1/8 W	
211	EC 100 µF/400 V	R14	R 0 Ω 1/4 W	
C12	C 1 µF/50 V	R15	R 10 KΩ 1/8 W	
C13	EC 1000 µF/10 V	R16	R 1 Ω 1/8 W	
214	EC 470 µF/10 V	R18	R 0 Ω 1/8 W	
C15	CC 100 pF/50 V	R19	R 100 Ω 1/8 W	
C16	C 1 nF/50 V	R20	R 1 KΩ 1/8 W	
C17	C 470 pF/50 V	R21	R 4.7 KΩ 1/8 W	
C18	EC 47 μF/50 V	R22	R 7.5 KΩ 1/8 W	
C19	C 0.01 µF/50 V	R23	R 120 KΩ 1/8 W	
C20	C 0.1 µF/50 V	R24	R 15 KΩ 1/8 W	
D1	FYP1010	R26	R 10 KΩ 1/8 W	
02	1N4148	R28	R 0.43 Ω 2 W	
03	FR107	TX1	800 µH(ERL-28)	
04	FR103	U1	IC FAN6605	
D5	FYP1010	U2	IC PC817	
ZD1	P6KE150A	U3	IC TL431	
-1	FUSE 4A/250 V			
<b>Л</b> 1	VZ 9G			
_1	13 mH			
2	Inductor (2 µH)			
_3	Inductor (2 µH)			

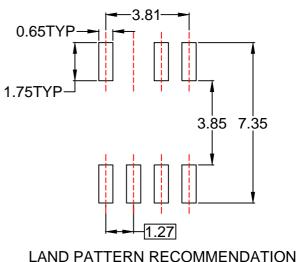


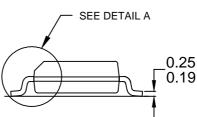
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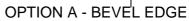
0.51

FRONT VIEW

0.10 C

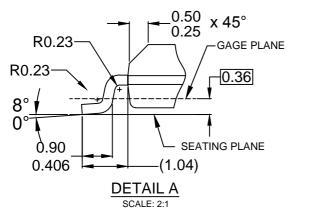








**OPTION B - NO BEVEL EDGE** 



0.25

0.10

1.75 MAX

NOTES:

- A) THIS PACKAGE DOES NOT FULLY CONFORMS TO JEDEC MS-012, VARIATION AA, ISSUE C.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) DRAWING FILENAME : M07Arev4.



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